

# EUV Pellicle Transmission Measurements

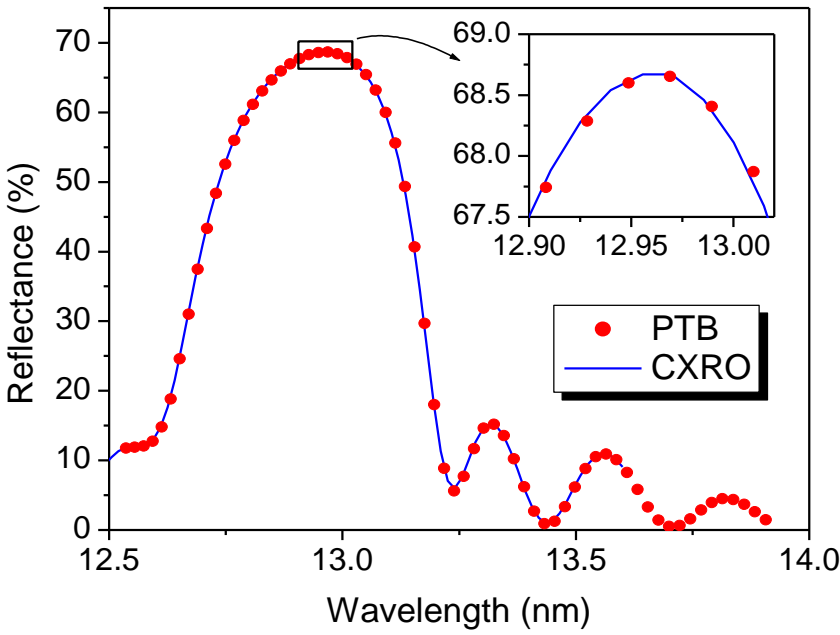
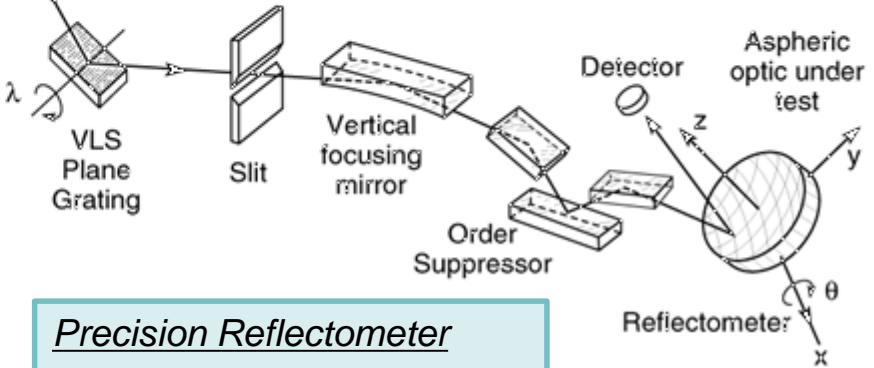
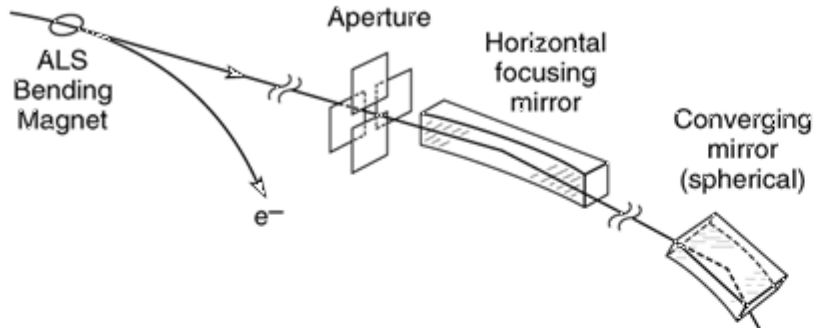
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# ALS Reflectometry and Scattering Beamline

Beamline Specifications

- 1-50 nm wavelength range
- Wavelength precision: 0.007%
- Wavelength uncertainty: 0.013%
- Reflectance precision: 0.08%
- Reflectance uncertainty: 0.08%
- Spectral purity: 99.98%
- Dynamic range:  $10^{10}$

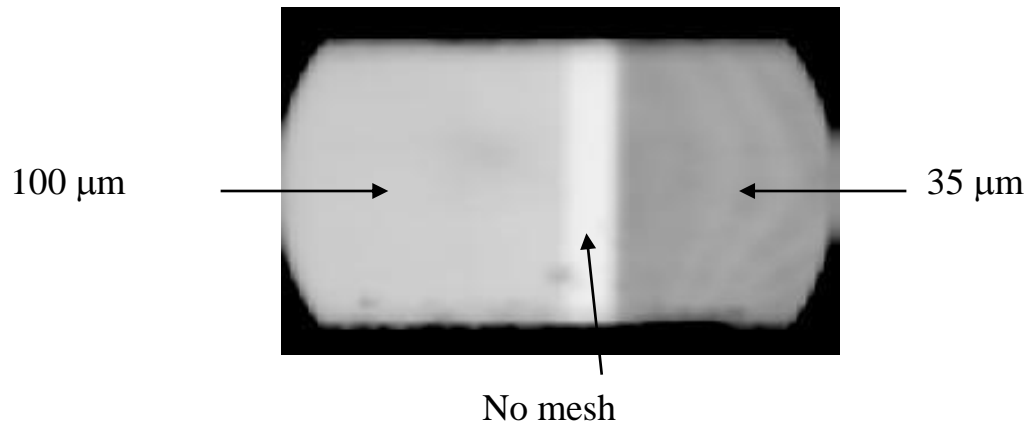


Precision Reflectometer

- $10 \times 150$  micron beam size
- 10 micron positioning
- Angular precision 0.01 deg
- 6 degrees of freedom
- Sample size up to 300 mm

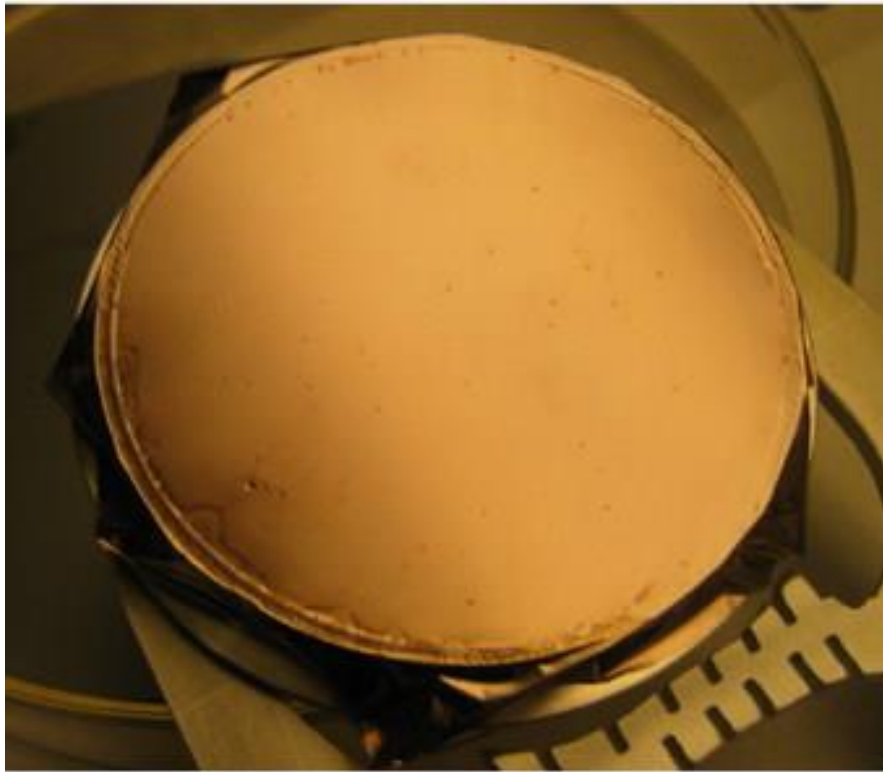
# Si Pellicle with 1 micron support mesh

| Linewidth ( $\mu\text{m}$ ) | Pitch ( $\mu\text{m}$ ) | $T_{\text{mesh}}$ expected | $T_{\text{mesh}}$ measured | $T_{\text{pellicle}}$ measured |
|-----------------------------|-------------------------|----------------------------|----------------------------|--------------------------------|
| 1                           | 35                      | 94%                        | 94.5%                      | 79.5%                          |
| 1                           | 100                     | 98%                        | 97.5%                      | 81.9%                          |

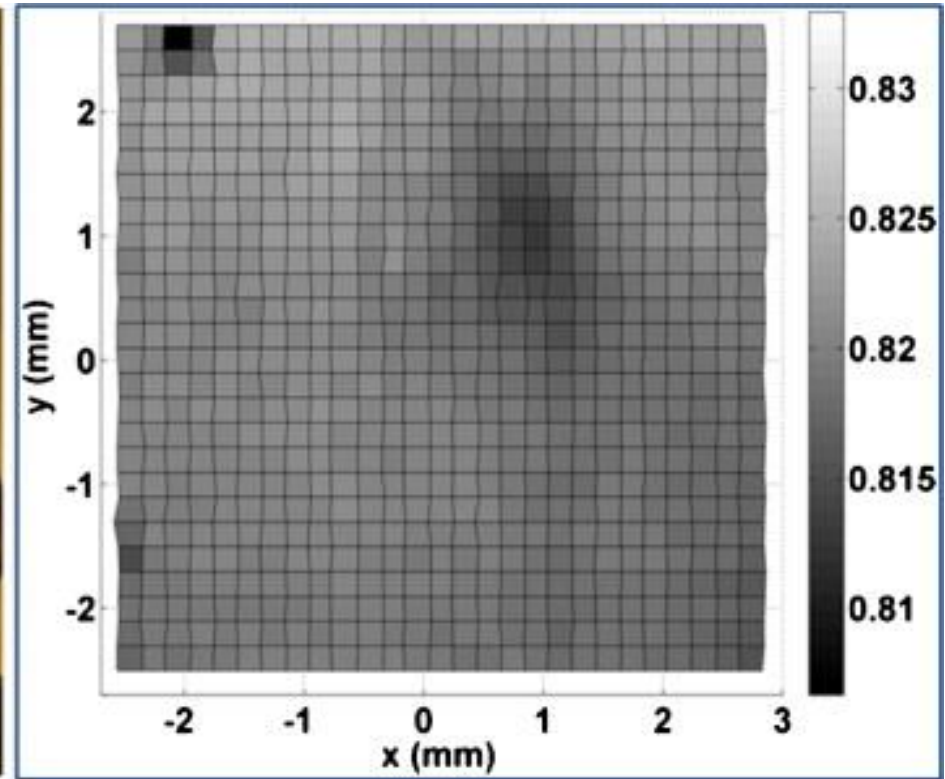


(50 nm Si + Ru cap Transmission = 84% at 13.5 nm.)

# Example: 75 mm diameter a-Si pellicle



(a)

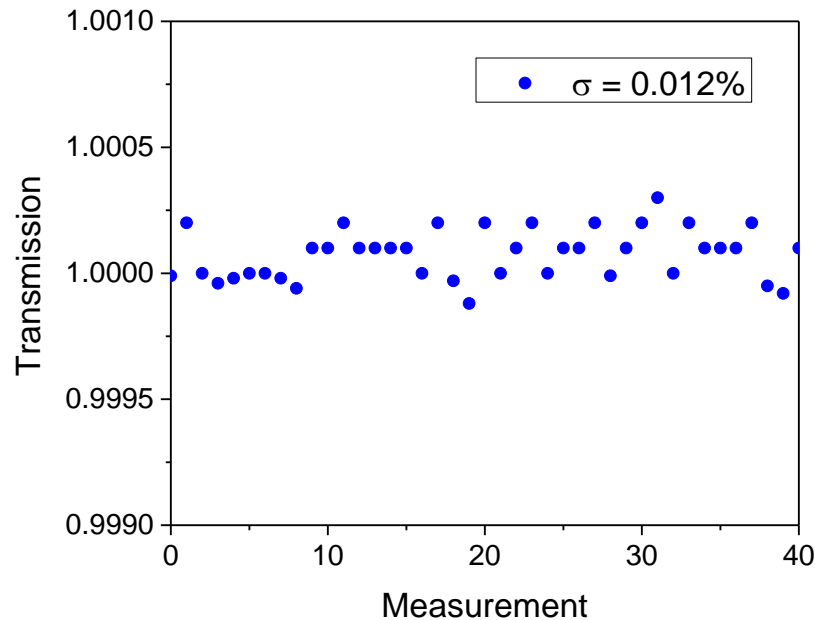


(b)

Wire-grid dimensions are 1/100  $\mu\text{m}$ , 50 nm Si with 2 nm Ru cap. EUV transmission 82% with 1.6% non-uniformity.

Y. Shroff, M Leeson, Pei-Yang Yan, E. Gullikson, F Salmassi, J. Vac. Sci. Technol. B 28, C6E36 (2010)

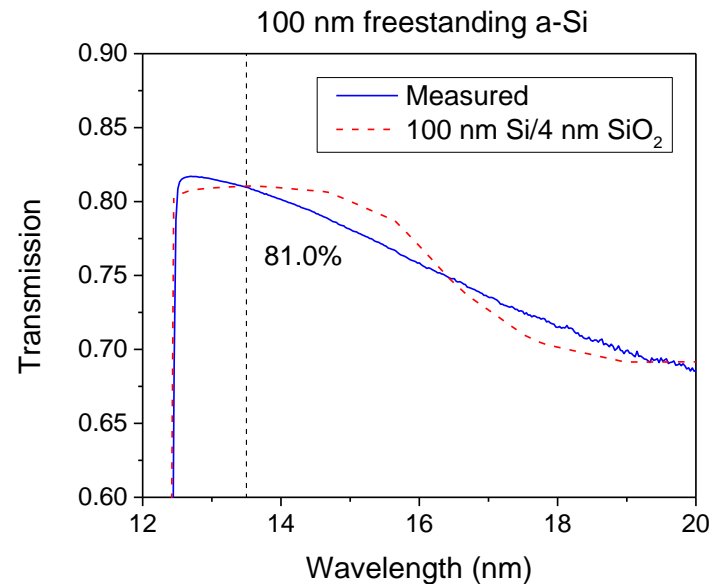
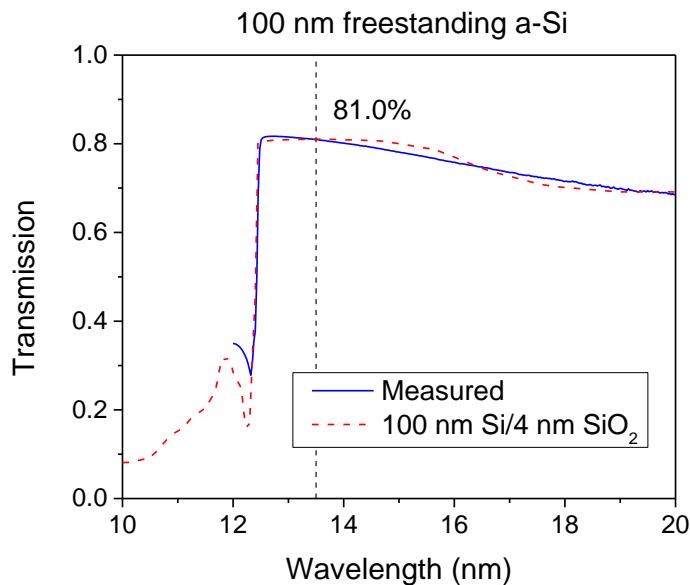
High precision and accuracy is available at the Synchrotron beamlines.



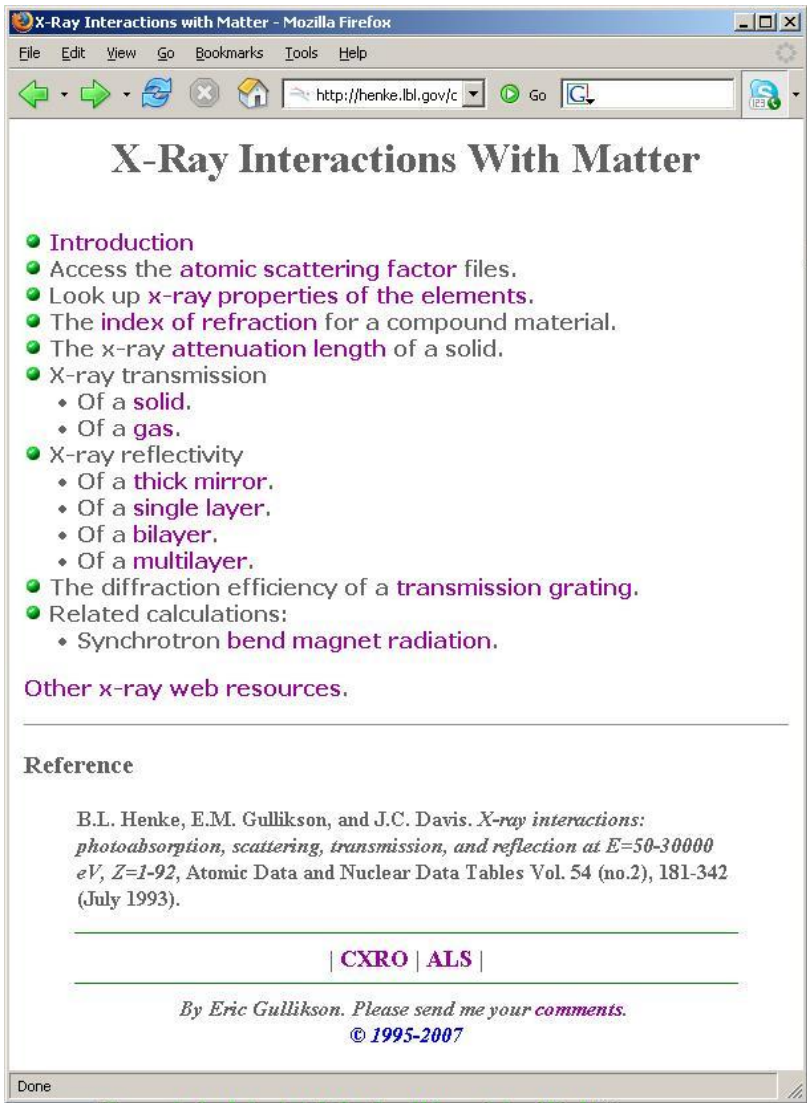
Measurements of pellicle uniformity  $< 0.2\%$  are possible.

# Wavelength dependence of freestanding Silicon

There is a difference between the amorphous Si deposited by Magnetron sputtering and the calculated transmission which is based on measurements of single crystal Silicon.



# Atomic scattering factors

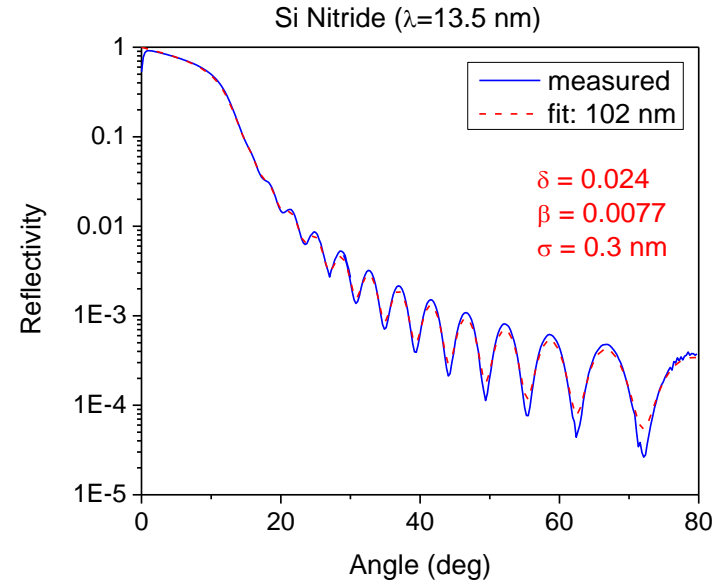
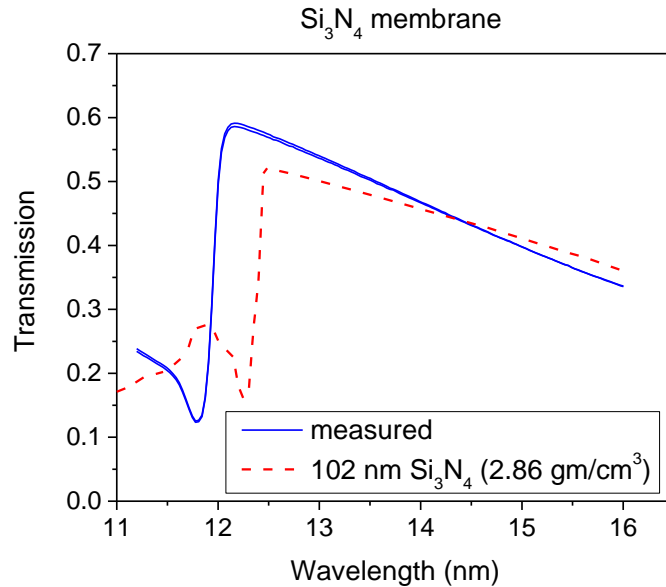


- [www.cxro.lbl.gov](http://www.cxro.lbl.gov)
- Worldwide standard reference
- More than 1 million accesses per year

- Measurements at  
Beamline 6.3.2*
- Be - R. Soufli *et al.*
  - Si - R. Soufli (*thesis*)
  - Mo - R. Soufli (*thesis*)
  - Mg - E. Gullikson *et al.*
  - Al - E. Gullikson *et al.*
  - Ru - U. Schlegel (*thesis*)
  - Y - B. Sae-Lao (*thesis*)
  - Pt - E. Gullikson *et al.*
  - Ir - D. Graessle *et al.*
  - Sc - A. Aquila *et al.*

# Transmission and reflectivity of silicon nitride

The film thickness and optical constants can be obtained from the reflectivity.



Edge is shifted to shorter wavelength.  
 Wavelength dependence is off.  
 Depends in stoichiometry and density.

$$T = \exp\left(-\frac{4\pi\beta}{\lambda} d\right)$$

$$T = 48\%$$



- High accuracy and precision transmission measurements can be made at the ALS.
- Transmission uniformity  $< 0.2\%$  is measurable.
- Some discrepancies are observed between the measured and modeled transmission using the atomic scattering factors.

Thank you!